2SK217

Silicon N-Channel Junction FET

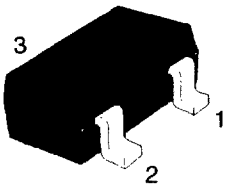
HITACHI

Application

VHF amplifier

Outline

MPAK



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Gate to drain current	V_{GDO}	–30	V
Drain current	I_D	20	mA
Gate current	I_G	10	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

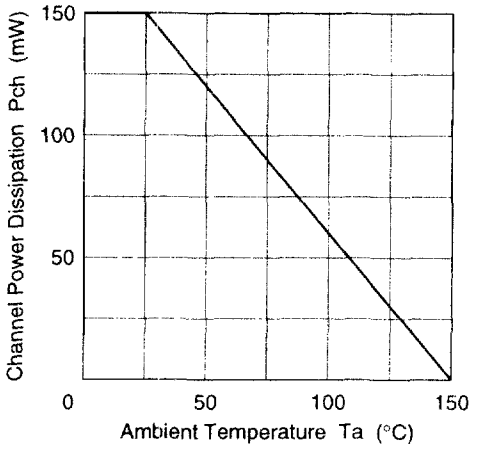
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Gate to drain breakdown voltage	$V_{(BR)GDO}$	–30	—	—	V	I_G = –100 µA
Gate cutoff current	I_{GSS}	—	—	–10	nA	V_{GS} = –0.5 V, V_{DS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	—	—	–2.5	V	V_{DS} = 5 V, I_D = 10 µA
Drain current	I_{DSS}*1	2.5	—	12	mA	V_{DS} = 5 V, V_{GS} = 0
Forward transfer admittance	$\|y_{fs}\|$	—	8.0	—	mS	V_{DS} = 5 V, V_{GS} = 0, f = 1 kHz
Reverse transfer capacitance	Crss	—	0.1	—	pF	V_{DS} = 5 V, V_{GS} = 0, f = 1 MHz

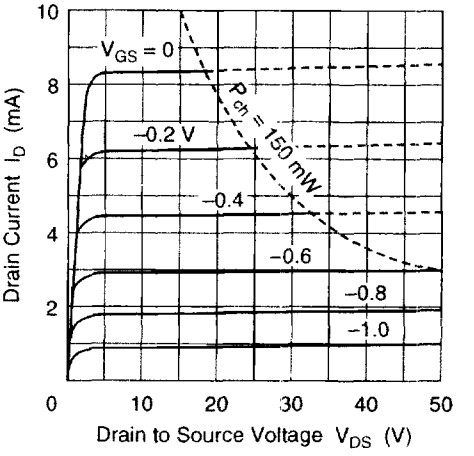
Note: 1. The 2SK217 is grouped by I_{DSS} as follows.

Grade	C	D	E
Mark	ZC	ZD	ZE
I_{DSS}	2.5 to 5	4 to 8	6 to 12

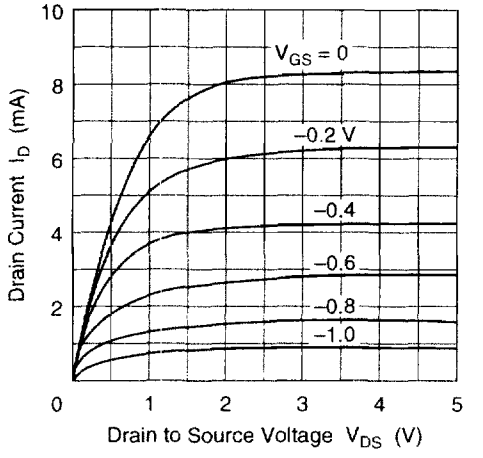
Maximum Channel Power Dissipation Curve



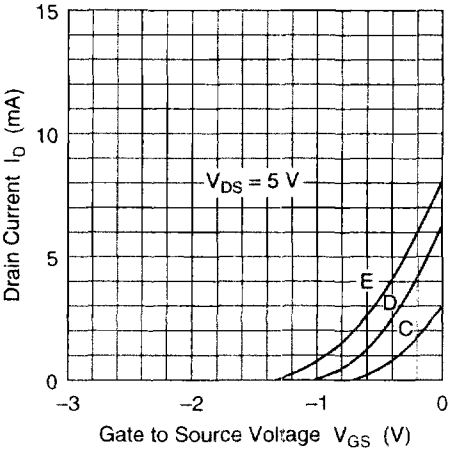
Typical Output Characteristics (1)



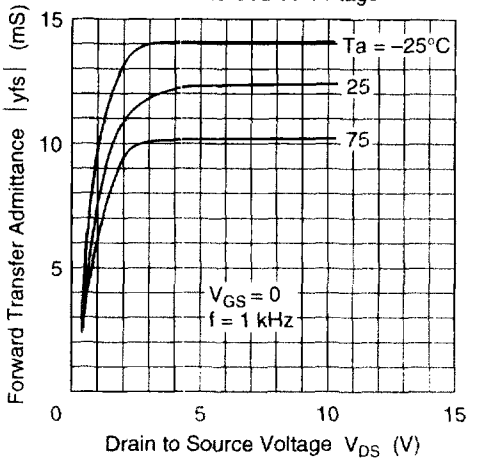
Typical Output Characteristics (2)



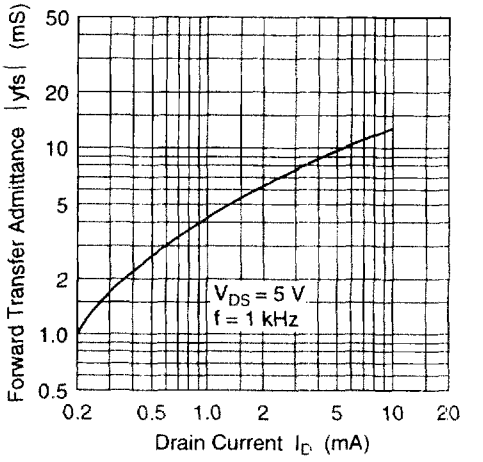
Typical Transfer Characteristics



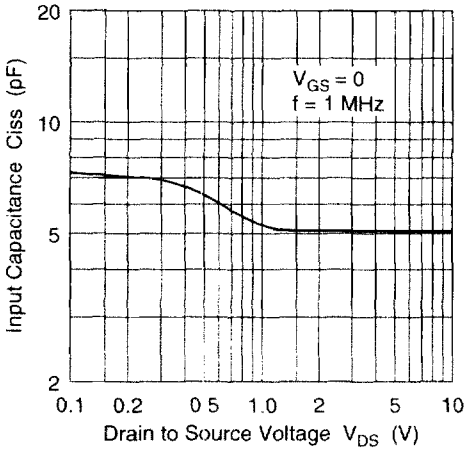
Forward Transfer Admittance vs.
Drain to Source Voltage



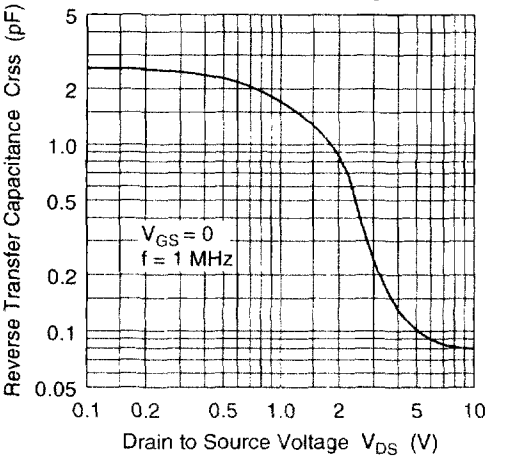
Forward Transfer Admittance vs.
Drain Current



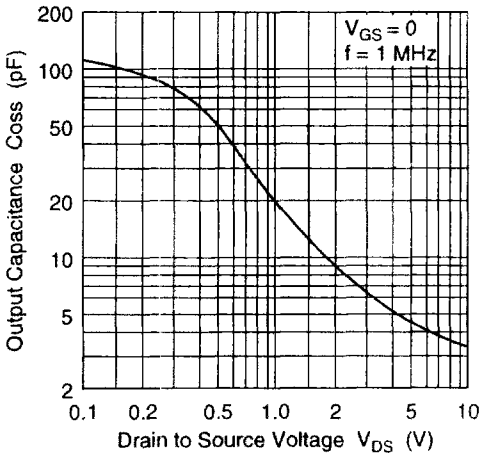
Input Capacitance vs.
Drain to Source Voltage



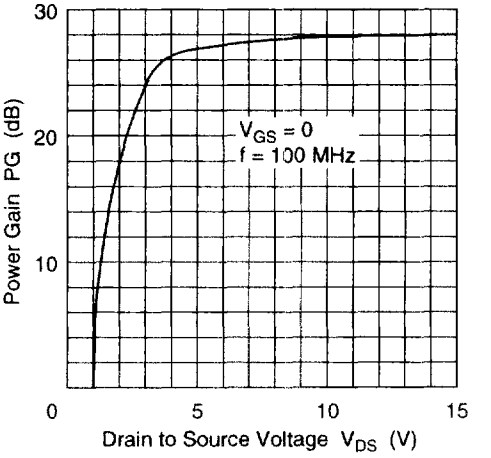
Reverse Transfer Capacitance vs.
Drain to Source Voltage



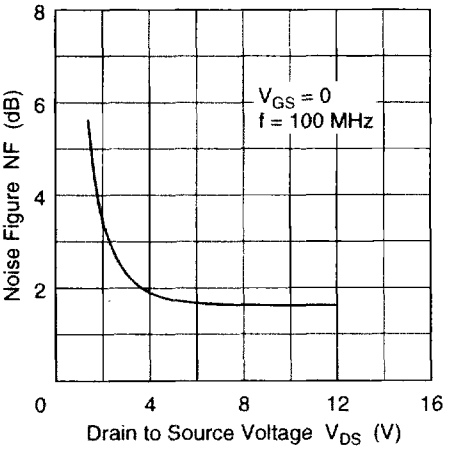
Output Capacitance vs.
Drain to Source Voltage



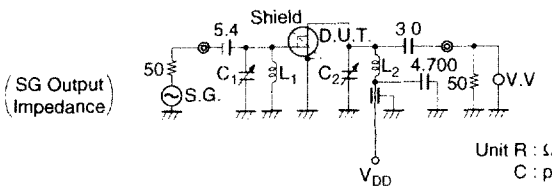
Power Gain vs.
Drain to Source Voltage



Noise Figure vs.
Drain to Source Voltage



Power Gain and Noise Figure
Test Circuit



C_1, C_2 : 0 to 30pF Variable Air
L_1 : 3.5 T φ1 mm Copper Ribbon, Tin plated 10 mm Inside dia.
L_2 : 4.5 T φ1 mm Copper Ribbon, Tin plated 10 mm Inside dia.